Claudio Goletti

List of Publications by Year
in descending order

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103	1,467	304743	434195
papers	citations	22 h-index	31 g-index

104	104	104	1171
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Reflectance anisotropy spectroscopy of strain-engineered GaAsBi alloys. Applied Physics Letters, 2022, 120, .	3.3	5
2	Unveiling the robustness of porphyrin crystalline nanowires toward aggressive chemicals. European Physical Journal Plus, 2022, 137, 1.	2.6	2
3	Nature of Optical Excitations in Porphyrin Crystals: A Joint Experimental and Theoretical Study. Journal of Physical Chemistry Letters, 2021, 12, 869-875.	4.6	4
4	Growth of Corrole Films from Solution: A Nanometer-Scale Study at the Real Solidâ€“Liquid Interface. Journal of Physical Chemistry C, 2021, 125, 11540-11547.	3.1	2
5	Substrate mediated interaction of terbium(<scp>iii</scp>) double-deckers with the TiO₂(110) surface. Physical Chemistry Chemical Physics, 2021, 23, 12060-12067.	2.8	4
6	Cobalt atoms drive the anchoring of Co-TPP molecules to the oxygen-passivated Fe(0â€¯0â€¯1) surface. Applied Surface Science, 2020, 505, 144213.	6.1	21
7	Evidence of graphite blister evolution during the anion de-intercalation process in the cathodic regime. Applied Surface Science, 2020, 504, 144440.	6.1	11
8	Tunable Supramolecular Chirogenesis in the Self-Assembling of Amphiphilic Porphyrin Triggered by Chiral Amines. International Journal of Molecular Sciences, 2020, 21, 8557.	4.1	5
9	Ordered assembling of Co tetra phenyl porphyrin on oxygen-passivated Fe(001): from single to multilayer films. EPJ Web of Conferences, 2020, 230, 00014.	0.3	3
10	Persistence of the Co-tetra-phenyl-porphyrin HOMO-LUMO features when a single organic layer is grown onto Cu(1Â1Â0)-(2ÂÃ—Â1)O. Applied Surface Science, 2020, 514, 145891.	6.1	6
11	Perimeter fractal dimension analysis of corrole islands on Au(111) at the solid-water interface. Journal of Porphyrins and Phthalocyanines, 2020, 24, 959-963.	0.8	3
12	In situ atomic force microscopy: the case study of graphite immersed in aqueous NaOH electrolyte. European Physical Journal Plus, 2020, 135, 1.	2.6	1
13	Islanding, growth mode and ordering in Si heteroepitaxy on Ge(001) substrates structured by thermal annealing. Surface Science, 2019, 683, 31-37.	1.9	2
14	Temperature Effects on the HOPG Intercalation Process. Condensed Matter, 2019, 4, 23.	1.8	4
15	Incipient Anion Intercalation of Highly Oriented Pyrolytic Graphite Close to the Oxygen Evolution Potential: A Combined X-ray Photoemission and Raman Spectroscopy Study. Journal of Physical Chemistry C, 2019, 123, 1790-1797.	3.1	18
16	The effect of cyclic voltammetry speed on anion intercalation in HOPG. Surface Science, 2019, 681, 111-115.	1.9	8
17	Reflectance Anisotropy Spectroscopy. , 2018, , 413-420.		1
18	Corroles at the Real Solidâ€“Liquid Interface: In Situ STM Investigation of a Waterâ€Soluble Corrole Layer Deposited onto Au(111). Chemistry - A European Journal, 2018, 24, 17538-17544.	3.3	5

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19	Reflectance anisotropy spectroscopy applied to organic thin films: The role of the substrate. Organic Electronics, 2018, 62, 102-106.	2.6	4
20	Formation of extended thermal etch pits on annealed Ge wafers. Applied Surface Science, 2018, 462, 86-94.	6.1	7
21	How to build an educational bridge. Nature Nanotechnology, 2017, 12, 1104-1104.	31.5	8
22	Molecular Ordering at the Interface Between Liquid Water and Rutile TiO₂(110). Advanced Materials Interfaces, 2015, 2, 1500246.	3.7	68
23	In situ scanning tunneling microscopy study of Ca-modified rutile TiO2(110) in bulk water. Beilstein Journal of Nanotechnology, 2015, 6, 438-443.	2.8	9
24	Cu(110) Surface in Hydrochloric Acid Solution: Potential Dependent Chloride Adsorption and Surface Restructuring. Journal of Physical Chemistry C, 2015, 119, 1782-1790.	3.1	29
25	Early oxidation stages of the strained Ge/Si(105) surface: A reflectance anisotropy spectroscopy study. Physica Status Solidi (B): Basic Research, 2015, 252, 87-94.	1.5	1
26	Surfaceâ˜Enhanced Polymerization via Schiff-Base Coupling at the Solidâ€“Water Interface under pH Control. Journal of Physical Chemistry C, 2015, 119, 19228-19235.	3.1	39
27	Probing Two-Dimensional vs Three-Dimensional Molecular Aggregation in Metal-Free Tetraphenylporphyrin Thin Films by Optical Anisotropy. Journal of Physical Chemistry C, 2014, 118, 15649-15655.	3.1	23
28	Optical Anisotropy of Thin and Ultrathin Porphyrin Layers. Topics in Heterocyclic Chemistry, 2014, , 53-115.	0.2	3
29	Intermixing and buried interfacial structure in strained Ge/Si(105) facets. Physical Review B, 2013, 88, .	3.2	16
30	Confinement effects in Ï€-bonded chains at group IV semiconductor (111) surfaces. Journal of Physics Condensed Matter, 2013, 25, 485008.	1.8	2
31	Charge transfer between isomer domains on n+-doped Si(111)-2 Ã— 1: energetic stabilization. Journal of Physics Condensed Matter, 2012, 24, 354009.	1.8	5
32	Site-Sensitive Gas Sensing and Analyte Discrimination in Langmuirâ˜Blodgett Porphyrin Films. Journal of Physical Chemistry C, 2011, 115, 8189-8194.	3.1	33
33	Coexistence of Negatively and Positively Buckled Isomers onn+-DopedSi(111)â˜2Ã—1. Physical Review Letters, 2011, 106, 067601.	7.8	27
34	Optical absorption measurements of electron quantum confinement in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>Si</mml:mtext><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mn>111</mml:mn></mml:mrow> chains. Physical Review B, 2010, 82, .	3.2	4
35	Reflectance anisotropy spectroscopy: A probe to explore organic epitaxial growth. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 1029-1034.	2.1	16
36	Optical anisotropy readout in solid-state porphyrins for the detection of volatile compounds. Applied Physics Letters, 2009, 95, 091906.	3.3	13

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37	Pseudomorphic growth of organic semiconductor thin films driven by incommensurate epitaxy. Applied Physics Letters, 2009, 94, 073307.	3.3	17
38	The -reconstructed cleavage surface of diamond: A challenging test for experiment and theory. Superlattices and Microstructures, 2009, 46, 227-233.	3.1	7
39	Dispersion of surface bands and chain coupling at Si and Ge(111) surfaces. Surface Science, 2008, 602, 1423-1427.	1.9	3
40	In-situ study of the interface formation in organic multilayers. Superlattices and Microstructures, 2008, 44, 550-555.	3.1	1
41	Growth-related properties and postgrowth phenomena in organic molecular thin films. Journal of Chemical Physics, 2007, 127, 244703.	3.0	10
42	Optical gap between dangling-bond states of a single-domain diamond C(111)-2 Ã— 1 by reflectance anisotropy spectroscopy. Europhysics Letters, 2007, 79, 57002.	2.0	20
43	Epitaxial growth of organic heterostructures: Morphology, structure, and growth mode. Surface Science, 2007, 601, 2571-2575.	1.9	18
44	A combined scanning tunneling microscopy and reflectance anisotropy spectroscopy investigation of tetraphenylporphyrin deposited on graphite. Surface Science, 2007, 601, 2607-2610.	1.9	15
45	Real time detection of the epitaxial growth of oligothiophene layers by reflectance anisotropy spectroscopy. Surface Science, 2007, 601, 4488-4491.	1.9	7
46	Direct observation of the epitaxial growth of molecular layers on molecular single crystals. Applied Physics Letters, 2006, 89, 261905.	3.3	19
47	Strategies for two-dimensional growth of organic molecular films. Chemical Physics, 2006, 325, 193-206.	1.9	33
48	AIRFLY: Measurement of the Air Fluorescence Radiation Induced by Electrons. Nuclear Physics, Section B, Proceedings Supplements, 2006, 150, 186-189.	0.4	6
49	AIRFLY: Measurement of the uorescence yield in atmospheric gases. European Physical Journal D, 2006, 56, A361-A367.	0.4	6
50	Detection of surface states anisotropies at GaAs(001)(2 Ã— 4) decapped surfaces. Physica Status Solidi (B): Basic Research, 2005, 242, 2664-2670.	1.5	1
51	Optical anisotropy and gas sensing properties of ordered porphyrin films. Physica Status Solidi (B): Basic Research, 2005, 242, 2714-2719.	1.5	14
52	Tuning the growth mode in organic molecular-beam epitaxy. Physical Review B, 2005, 71, .	3.2	23
53	Infrared reflectance anisotropy spectroscopy ofSi(111)â˜2Ã—1: Surface excitons and polarons. Physical Review B, 2005, 72, .	3.2	7
54	Surfaces and Interfaces, Electronic Structure of. , 2005, , 133-144.		1

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55	Optical transitions and sum rules at clean semiconductor surfaces. Journal of Physics Condensed Matter, 2004, 16, S4289-S4300.	1.8	15
56	Optical anisotropy of Cs nanostructures on IIIâ€“V(110) surfaces. Journal of Physics Condensed Matter, 2004, 16, S4353-S4365.	1.8	3
57	In situoptical investigation of oligothiophene layers grown by organic molecular beam epitaxy. Journal of Physics Condensed Matter, 2004, 16, S4393-S4402.	1.8	12
58	Surface states at theGaAs(001)2Ã—4surface. Physical Review B, 2004, 69, .	3.2	19
59	The application of reflectance anisotropy spectroscopy to organics deposition. Organic Electronics, 2004, 5, 73-81.	2.6	40
60	Spontaneous deposition of amphiphilic porphyrin films on glassElectronic supplementary information (ESI) available: detailed kinetic studies and procedures, and aggregation studies on 1H2 and 2H2. See http://www.rsc.org/suppdata/nj/b4/b403591g/. New Journal of Chemistry, 2004, 28, 1123.	2.8	34
61	Highly sensitive optical monitoring of molecular film growth by organic molecular beam deposition. Applied Physics Letters, 2003, 83, 4146-4148.	3.3	37
62	Surface versus bulk contributions from reflectance anisotropy and electron energy loss spectra of theGaAs(001)â˜c(4Ã—4)surface. Physical Review B, 2003, 68, .	3.2	22
63	Optical resonances of indium islands on GaAs(001) observed by reflectance anisotropy spectroscopy. Physical Review B, 2003, 67, .	3.2	20
64	Ge growth on GaAs(001) surfaces studied by reflectance anisotropy spectroscopy. Physical Review B, 2002, 66, .	3.2	6
65	Thickness Dependence of the Optical Anisotropy for Porphyrin Octaester Langmuirâ˜Schaefer Filmsâ€. Langmuir, 2002, 18, 6881-6886.	3.5	34
66	Infrared surface absorption inSi(111)2Ã—1observed with reflectance anisotropy spectroscopy. Physical Review B, 2002, 66, .	3.2	33
67	Optical anisotropy of porphyrin Langmuirâ€“Blodgett films. Surface Science, 2002, 501, 31-36.	1.9	26
68	Langmuirâ€“Blodgett films of a modified tetraphenylporphyrin. Materials Science and Engineering C, 2002, 22, 219-225.	7.3	9
69	Optical anisotropy of oxidized InAs() surfaces. Surface Science, 2002, 515, 281-286.	1.9	7
70	Structure-dependent optical anisotropy of porphyrin Langmuirâ€“Schaefer films. Surface Science, 2002, 521, L645-L649.	1.9	5
71	A Reflectance Anisotropy Spectroscopy Investigation of Porphyrin Langmuir-Blodgett Films. Physica Status Solidi A, 2001, 188, 1339-1344.	1.7	6
72	Sum rules in surface differential reflectivity and reflectance anisotropy spectroscopies. Applied Surface Science, 2001, 175-176, 777-782.	6.1	8

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73	Analysis of InAs(001) surfaces by reflectance anisotropy spectroscopy. Physical Review B, 2001, 64, .	3.2	25
74	Optical Anisotropy of Clean and Oxidized GaAs(001)-4 Ã— 2. , 2001, , .		0
75	STUDY OF THE OPTICAL ANISOTROPY OF LANGMUIR-BLODGETT FILMS OF EXTENDED PYRROLIC MACROCYCLES USED IN GAS SENSORS DEVICES. , 2000, , .		0
76	Chemical sensing materials characterization by Kelvin probe technique. Sensors and Actuators B: Chemical, 2000, 70, 254-262.	7.8	25
77	Optical characterization of indium-terminated GaAs(001) surfaces. Physical Review B, 2000, 61, 1681-1684.	3.2	12
78	Optical anisotropy of Langmuirâ€“Blodgett sapphyrin films. Applied Physics Letters, 2000, 77, 3164-3166.	3.3	28
79	Sum rules in surface reflectivity: the case of Ge(111)-(2Ã—1) and Si(111)-(2Ã—1). Surface Science, 2000, 453, 112-118.	1.9	22
80	Kelvin probe and scanning tunneling microscope characterization of Langmuirâ€“Blodgett sapphyrin films. Applied Physics Letters, 1999, 75, 1237-1239.	3.3	17
81	Kelvin probe investigation of the thickness effects in Langmuirâ€“Blodgett films of pyrrolic macrocycles sensitive to volatile compounds in gas phase. Sensors and Actuators B: Chemical, 1999, 57, 183-187.	7.8	14
82	Ge/GaAs(001) interface formation investigated by reflectance anisotropy spectroscopy. Physical Review B, 1999, 59, 10657-10661.	3.2	12
83	Origin of the optical anisotropy of GaAs (001). Surface Science, 1999, 441, 26-32.	1.9	35
84	Optical properties of bismuth-terminatedGaAs(110) surfaces. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1998, 20, 975-980.	0.4	1
85	Characterization and design of porphyrins-based broad selectivity chemical sensors for electronic nose applications. Sensors and Actuators B: Chemical, 1998, 52, 162-168.	7.8	65
86	Optical anisotropies of InP(001) surfaces. Journal of Applied Physics, 1997, 81, 3611-3615.	2.5	17
87	Surface reflectance anisotropy of indium-terminated GaAs(100) surfaces. Surface Science, 1997, 377-379, 404-408.	1.9	4
88	A reflectance anisotropy spectroscopy study of GaSb(100)c(2 Ã— 6) surfaces prepared by Sb decapping. Surface Science, 1996, 352-354, 771-775.	1.9	21
89	Activated chemisorption of oxygen on Si(111)-2 Ã— 1. Surface Science, 1996, 356, 68-74.	1.9	12
90	Schottky barrier at the Au/Gap (110) interface. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 2433-2436.	2.1	1

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91	Nearly flat bands at the GaP(110) surface. Physical Review B, 1995, 52, 10721-10724.	3.2	3
92	Optical anisotropy of ordered Sb layers on III-V (110) surfaces. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1994, 70, 507-519.	0.6	13
93	Polarization-dependent surface transitions at (110). Solid State Communications, 1993, 85, 497-500.	1.9	10
94	Schottky barrier and surface photovoltage induced by synchrotron radiation in GaP(110)/Ag. Physical Review B, 1993, 47, 13520-13526.	3.2	14
95	Antimony-induced optical transitions of the Sb/GaAs(110) interface. Solid State Communications, 1992, 84, 421-425.	1.9	14
96	Polarized surface differential reflectivity and oxygen chemisorption on InP(110) surfaces. Surface Science, 1991, 251-252, 281-285.	1.9	2
97	Surface-state band gap of InP(110) by polarized surface differential reflectivity. Physical Review B, 1991, 44, 8327-8329.	3.2	15
98	Oxygen chemisorption on cleaved InP(110) surfaces studied with surface differential reflectivity. Physical Review B, 1991, 43, 6757-6759.	3.2	9
99	Clean and oxygen covered InP(110) surfaces differential reflectivity. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 1026-1028.	2.1	10
100	Surface optical transitions on cleaved InP(110). Surface Science, 1989, 211-212, 552-556.	1.9	21
101	Determination of the complex dielectric function of Si(111) 2 Ã— 1, GaAs(110) and GaP(110) surfaces by polarized surface differential reflectivity. Physica Scripta, 1988, 38, 199-203.	2.5	29
102	Dielectric functions of Si(111)2Ã—1, Ge(111)2Ã—1, GaAs(110) and GaP(110) surfaces obtained by polarized surface differential reflectivity. Surface Science, 1987, 189-190, 1023-1027.	1.9	26
103	Polarization dependence of optical transitions in GaP(1 1 0) and GaAs(1 1 0) surfaces studied with surface differential reflectivity. Solid State Communications, 1987, 62, 833-834.	1.9	33